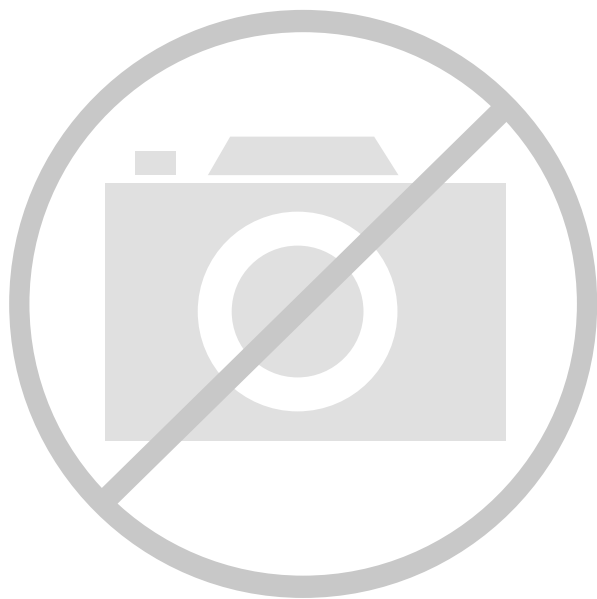




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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details

Product Status	Active
Architecture	MCU, FPGA
Core Processor	Quad ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™, ARM Mali™-400 MP2
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	533MHz, 600MHz, 1.3GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 1143K+ Logic Cells
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	1924-BBGA, FCBGA
Supplier Device Package	1924-FCBGA (45x45)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu19eg-2ffve1924i

Table 4: DC Characteristics Over Recommended Operating Conditions (Cont'd)

Symbol	Description	Min	Typ ⁽¹⁾	Max	Units
I_{CC_PSBATT} ⁽⁴⁾⁽⁵⁾	Battery supply current at $V_{CC_PSBATT} = 1.50V$, RTC enabled.	–	–	3650	nA
	Battery supply current at $V_{CC_PSBATT} = 1.50V$, RTC disabled.	–	–	650	nA
	Battery supply current at $V_{CC_PSBATT} = 1.20V$, RTC enabled.	–	–	3150	nA
	Battery supply current at $V_{CC_PSBATT} = 1.20V$, RTC disabled.	–	–	150	nA
I_{PSFS} ⁽⁶⁾	PS V_{CC_PSAUX} additional supply current during eFUSE programming.	–	–	115	mA
<i>Calibrated programmable on-die termination (DCI) in HP I/O banks⁽⁸⁾ (measured per JEDEC specification)</i>					
R ⁽⁹⁾	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where $ODT = RTT_{40}$.	–10% ⁽⁷⁾	40	+10% ⁽⁷⁾	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where $ODT = RTT_{48}$.	–10% ⁽⁷⁾	48	+10% ⁽⁷⁾	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where $ODT = RTT_{60}$.	–10% ⁽⁷⁾	60	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{40}$.	–10% ⁽⁷⁾	40	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{48}$.	–10% ⁽⁷⁾	48	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{60}$.	–10% ⁽⁷⁾	60	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{120}$.	–10% ⁽⁷⁾	120	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{240}$.	–10% ⁽⁷⁾	240	+10% ⁽⁷⁾	Ω
<i>Uncalibrated programmable on-die termination in HP I/Os banks (measured per JEDEC specification)</i>					
R ⁽⁹⁾	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where $ODT = RTT_{40}$.	–50%	40	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where $ODT = RTT_{48}$.	–50%	48	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where $ODT = RTT_{60}$.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{40}$.	–50%	40	+50%	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{48}$.	–50%	48	+50%	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{60}$.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{120}$.	–50%	120	+50%	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{240}$.	–50%	240	+50%	Ω
<i>Uncalibrated programmable on-die termination in HD I/O banks (measured per JEDEC specification)</i>					
R ⁽⁹⁾	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where $ODT = RTT_{48}$.	–50%	48	+50%	Ω
Internal V_{REF}	50% V_{CCO}	$V_{CCO} \times 0.49$	$V_{CCO} \times 0.50$	$V_{CCO} \times 0.51$	V
	70% V_{CCO}	$V_{CCO} \times 0.69$	$V_{CCO} \times 0.70$	$V_{CCO} \times 0.71$	V

PS-PL Power Sequencing

The PS and PL power supplies are fully independent. All PS power supplies can be powered before or after any PL power supplies. The PS and PL power regions are isolated to prevent damage.

Power Supply Requirements

Table 10 shows the minimum current, in addition to I_{CCQ} maximum, required by each Zynq UltraScale+ device for proper power-on and configuration. If the current minimums shown in Table 10 are met, the device powers on after all supplies have passed through their power-on reset threshold voltages. The device must not be configured until after V_{CCINT} is applied. Once initialized and configured, use the Xilinx Power Estimator (XPE) tools to estimate current drain on these supplies.

Table 10: Power-on Current by Device⁽¹⁾

I_{CC} Min =	I_{CCQ} +	XCZU2	XCZU3	XCZU4	XCZU5	XCZU6	XCZU7	XCZU9	XCZU11	XCZU15	XCZU17	XCZU19	Units
$I_{CCINTMIN}$	I_{CCINTQ}^+	464	464	770	770	1800	1514	1800	1961	2242	3433	3433	mA
$I_{CCINT_IOMIN}^+$ $I_{CCBRAMMIN}$	$I_{CCBRAMQ}^+$ $I_{CCINT_IOQ}^+$	155	155	257	257	600	505	600	654	748	1145	1145	mA
I_{CCOMIN}	I_{CCOQ}^+	50	50	50	50	50	50	50	55	63	96	96	mA
$I_{CCAUXMIN}^+$ I_{CCAUX_IOMIN}	I_{CCAUXQ}^+ $I_{CCAUX_IOQ}^+$	111	111	386	386	650	362	650	709	810	1240	1240	mA

Notes:

1. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate power-on current for all supplies.

Table 11 shows the power supply ramp time.

Table 11: Power Supply Ramp Time

Symbol	Description	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 95% of V_{CCINT} .	0.2	40	ms
T_{VCCINT_IO}	Ramp time from GND to 95% of V_{CCINT_IO} .	0.2	40	ms
T_{VCCINT_VCU}	Ramp time from GND to 95% of V_{CCINT_VCU} .	0.2	40	ms
T_{VCCO}	Ramp time from GND to 95% of V_{CCO} .	0.2	40	ms
T_{VCCAUX}	Ramp time from GND to 95% of V_{CCAUX} .	0.2	40	ms
$T_{VCCBRAM}$	Ramp time from GND to 95% of V_{CCBRAM} .	0.2	40	ms
$T_{MGTAVCC}$	Ramp time from GND to 95% of $V_{MGTAVCC}$.	0.2	40	ms
$T_{MGTAVTT}$	Ramp time from GND to 95% of $V_{MGTAVTT}$.	0.2	40	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 95% of $V_{MGTVCCAUX}$.	0.2	40	ms
$T_{VCC_PSINTFP}$	Ramp time from GND to 95% of $V_{CC_PSINTFP}$.	0.2	40	ms
$T_{VCC_PSINTLP}$	Ramp time from GND to 95% of $V_{CC_PSINTLP}$.	0.2	40	ms
T_{VCC_PSAUX}	Ramp time from GND to 95% of V_{CC_PSAUX} .	0.2	40	ms
$T_{VCC_PSINTFP_DDR}$	Ramp time from GND to 95% of $V_{CC_PSINTFP_DDR}$.	0.2	40	ms
T_{VCC_PSADC}	Ramp time from GND to 95% of V_{CC_PSADC} .	0.2	40	ms
T_{VCC_PSPLL}	Ramp time from GND to 95% of V_{CC_PSPLL} .	0.2	40	ms
$T_{PS_MGTRAVCC}$	Ramp time from GND to 95% of $V_{CC_MGTRAVCC}$.	0.2	40	ms
$T_{PS_MGTRAVTT}$	Ramp time from GND to 95% of $V_{CC_MGTRAVTT}$.	0.2	40	ms

Table 11: Power Supply Ramp Time (Cont'd)

Symbol	Description	Min	Max	Units
$T_{V_{CCO_PSDDR}}$	Ramp time from GND to 95% of V_{CCO_PSDDR} .	0.2	40	ms
$T_{V_{CC_PSDDR_PLL}}$	Ramp time from GND to 95% of $V_{CC_PSDDR_PLL}$.	0.2	40	ms
$T_{V_{CCO_PSIO}}$	Ramp time from GND to 95% of V_{CCO_PSIO} .	0.2	40	ms

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

PS I/O Levels

Table 12: PS MIO and CONFIG DC Input and Output Levels⁽¹⁾

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
LVC MOS33	-0.300	0.800	2.000	V_{CCO_PSIO}	0.40	2.40	12	-12
LVC MOS25	-0.300	0.700	1.700	$V_{CCO_PSIO} + 0.30$	0.70	1.70	12	-12
LVC MOS18	-0.300	35% V_{CCO_PSIO}	65% V_{CCO_PSIO}	$V_{CCO_PSIO} + 0.30$	0.45	$V_{CCO_PSIO} - 0.45$	12	-12

Notes:

1. Tested according to relevant specifications.

Table 13: PS DDR DC Input and Output Levels⁽¹⁾

DDR Standard	V_{IL}		V_{IH}		$V_{OL}^{(2)}$	$V_{OH}^{(2)}$	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
DDR4	0.000	$V_{REF} - 0.100$	$V_{REF} + 0.100$	V_{CCO_PSDDR}	$0.8 \times V_{CCO_PSDDR} - 0.150$	$0.8 \times V_{CCO_PSDDR} + 0.150$	10	-0.1
LPDDR4	0.000	$V_{REF} - 0.100$	$V_{REF} + 0.100$	V_{CCO_PSDDR}	$0.3 \times V_{CCO_PSDDR} - 0.150$	$0.3 \times V_{CCO_PSDDR} + 0.150$	0.1	-10
DDR3	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	V_{CCO_PSDDR}	$0.5 \times V_{CCO_PSDDR} - 0.175$	$0.5 \times V_{CCO_PSDDR} + 0.175$	8	-8
LPDDR3	0.000	$V_{REF} - 0.100$	$V_{REF} + 0.100$	V_{CCO_PSDDR}	$0.5 \times V_{CCO_PSDDR} - 0.150$	$0.5 \times V_{CCO_PSDDR} + 0.150$	8	-8
DDR3L	-0.300	$V_{REF} - 0.090$	$V_{REF} + 0.090$	V_{CCO_PSDDR}	$0.5 \times V_{CCO_PSDDR} - 0.150$	$0.5 \times V_{CCO_PSDDR} + 0.150$	8	-8

Notes:

1. Tested according to relevant specifications.
2. DDR4 V_{OL}/V_{OH} specifications are only applicable for DQ/DQS pins.

Table 15: SelectIO DC Input and Output Levels for HP I/O Banks⁽¹⁾⁽²⁾⁽³⁾

I/O Standard	V _{IL}		V _{IH}		V _{OL}	V _{OH}	I _{OL}	I _{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	−0.300	V _{REF} − 0.100	V _{REF} + 0.100	V _{CCO} + 0.300	0.400	V _{CCO} − 0.400	5.8	−5.8
HSTL_I_12	−0.300	V _{REF} − 0.080	V _{REF} + 0.080	V _{CCO} + 0.300	25% V _{CCO}	75% V _{CCO}	4.1	−4.1
HSTL_I_18	−0.300	V _{REF} − 0.100	V _{REF} + 0.100	V _{CCO} + 0.300	0.400	V _{CCO} − 0.400	6.2	−6.2
HSUL_12	−0.300	V _{REF} − 0.130	V _{REF} + 0.130	V _{CCO} + 0.300	20% V _{CCO}	80% V _{CCO}	0.1	−0.1
LVC MOS12	−0.300	35% V _{CCO}	65% V _{CCO}	V _{CCO} + 0.300	0.400	V _{CCO} − 0.400	Note 4	Note 4
LVC MOS15	−0.300	35% V _{CCO}	65% V _{CCO}	V _{CCO} + 0.300	0.450	V _{CCO} − 0.450	Note 5	Note 5
LVC MOS18	−0.300	35% V _{CCO}	65% V _{CCO}	V _{CCO} + 0.300	0.450	V _{CCO} − 0.450	Note 5	Note 5
LVDCI_15	−0.300	35% V _{CCO}	65% V _{CCO}	V _{CCO} + 0.300	0.450	V _{CCO} − 0.450	7.0	−7.0
LVDCI_18	−0.300	35% V _{CCO}	65% V _{CCO}	V _{CCO} + 0.300	0.450	V _{CCO} − 0.450	7.0	−7.0
SSTL12	−0.300	V _{REF} − 0.100	V _{REF} + 0.100	V _{CCO} + 0.300	V _{CCO} /2 − 0.150	V _{CCO} /2 + 0.150	8.0	−8.0
SSTL135	−0.300	V _{REF} − 0.090	V _{REF} + 0.090	V _{CCO} + 0.300	V _{CCO} /2 − 0.150	V _{CCO} /2 + 0.150	9.0	−9.0
SSTL15	−0.300	V _{REF} − 0.100	V _{REF} + 0.100	V _{CCO} + 0.300	V _{CCO} /2 − 0.175	V _{CCO} /2 + 0.175	10.0	−10.0
SSTL18_I	−0.300	V _{REF} − 0.125	V _{REF} + 0.125	V _{CCO} + 0.300	V _{CCO} /2 − 0.470	V _{CCO} /2 + 0.470	7.0	−7.0
MIPI_DPHY_DCI_LP ⁽⁶⁾	−0.300	0.550	0.880	V _{CCO} + 0.300	0.050	1.100	0.01	−0.01

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* ([UG571](#)).
3. POD10 and POD12 DC input and output levels are shown in [Table 16](#), [Table 20](#), [Table 21](#), and [Table 22](#).
4. Supported drive strengths of 2, 4, 6, or 8 mA in HP I/O banks.
5. Supported drive strengths of 2, 4, 6, 8, or 12 mA in HP I/O banks.
6. Low-power option for MIPI_DPHY_DCI.

Table 16: DC Input Levels for Single-ended POD10 and POD12 I/O Standards⁽¹⁾⁽²⁾

I/O Standard	V _{IL}		V _{IH}	
	V, Min	V, Max	V, Min	V, Max
POD10	−0.300	V _{REF} − 0.068	V _{REF} + 0.068	V _{CCO} + 0.300
POD12	−0.300	V _{REF} − 0.068	V _{REF} + 0.068	V _{CCO} + 0.300

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* ([UG571](#)).

Table 31: PS NAND NV-DDR Synchronous Performance

Memory Standard	Mode	Speed Grade			Units
		-3	-2	-1	
		Max	Max	Max	
NV-DDR ⁽¹⁾	5	200	200	200	Mb/s
	4	166.6	166.6	166.6	Mb/s
	3	133.3	133.3	133.3	Mb/s
	2	100	100	100	Mb/s
	1	66.6	66.6	66.6	Mb/s
	0	40	40	40	Mb/s

Notes:

1. The PS NAND memory controller interface for NV-DDR switching characteristics meets the requirements of the ONFI 3.1 specification.

Table 32: PS NAND SDR Asynchronous Performance

Memory Standard	Mode	Speed Grade			Units
		-3	-2	-1	
		Max	Max	Max	
SDR ⁽¹⁾⁽²⁾	5	50	50	50	Mb/s
	4	40	40	40	Mb/s
	3	33.3	33.3	33.3	Mb/s
	2	28.5	28.5	28.5	Mb/s
	1	20	20	20	Mb/s
	0	10	10	10	Mb/s

Notes:

1. The PS NAND memory controller interface for SDR switching characteristics meets the requirements of the ONFI 3.1 specification.
2. The NAND controller reference clock frequency maximum is 83 MHz.

Table 33: PS-PL Interface Performance

Symbol	Description	Min	Max	Units
F _{EMIOGEMCLK}	EMIO gigabit Ethernet controller maximum frequency.	–	125	MHz
F _{EMIOSDCLK}	EMIO SD controller maximum frequency.	–	25	MHz
F _{EMIOSPICLK}	EMIO SPI controller maximum frequency.	–	25	MHz
F _{EMIOTRACECLK}	EMIO trace controller maximum frequency.	–	125	MHz
F _{FCIDMACLK}	Flow control interface DMA maximum frequency.	–	333	MHz
F _{AXICLK}	Maximum AXI interface performance.	–	333	MHz
F _{DPLIVEVIDEO}	DisplayPort controller live video interface maximum frequency.	–	300	MHz

PS Switching Characteristics

PS Clocks

Table 34: PS Reference Clock Requirements⁽¹⁾

Symbol	Description	Min	Typ	Max	Units
T _{RMSJPCLK}	PS_REF_CLK input RMS clock jitter.	–	–	3	ps
T _{PJPCLK}	PS_REF_CLK input period jitter (peak-to-peak). Number of clock cycles = 10,000	–	–	50	ps
T _{DCPCLK}	PS_REF_CLK duty cycle.	45	–	55	%
T _{RFPSCLK}	PS_REF_CLK rise time (20%–80%) and fall time (80%–20%).	–	–	2.22	ns
F _{PSCLK}	PS_REF_CLK frequency.	27	–	60	MHz

Notes:

- The values in this table are applicable to alternative PS reference clock inputs ALT_REF_CLK, AUX_REF_CLK, and VIDEO_CLK.

Table 35: PS RTC Crystal Requirements⁽¹⁾

Symbol	Description	Min	Typ	Max	Units
F _{XTAL}	Parallel resonance crystal frequency.	–	32.8	–	KHz
T _{FTXTAL}	Frequency tolerance.	–20	–	20	ppm
C _{XTAL}	Load capacitance for crystal parallel resonance.	–	12.5	–	pF
R _{ESR}	Crystal ESR (16.8 and 19.2 MHz).	–	70	–	KΩ
C _{SHUNT}	Crystal shunt capacitance.	–	1.4	–	pF

Notes:

- Required board components: Feedback resistor = 4.7 MΩ, PCB and pad capacitance = 1.5 pF, C₁ and C₂ capacitance = 21 pF.

Table 36: PS PLL Switching Characteristics

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
F _{LOCKPSPLL}	PLL maximum lock time.	100	100	100	μs
F _{PSPLLMAX}	PLL maximum output frequency.	1600	1600	1600	MHz
F _{PSPLLMIN}	PLL minimum output frequency.	750	750	750	MHz
F _{PSPLLVCOMAX}	PLL maximum VCO frequency.	3000	3000	3000	MHz
F _{PSPLLVCOMIN}	PLL minimum VCO frequency.	1500	1500	1500	MHz

PS Triple-timer Counter Interface

Table 54: Triple-timer Counter Interface

Symbol	Description	Min	Max	Units
$T_{PWTTCOCLK}$	Triple-timer counter output clock pulse width.	60.4	—	ns
$F_{TTCOCLK}$	Triple-timer counter output clock frequency.	—	16.5	MHz
$T_{TTCICLKHL}$	Triple-timer counter input clock high pulse width.	$1.5 \times 1/F_{LPD_LSBUS_CTRLMAX}$	—	ns
$T_{TTCICLKHL}$	Triple-timer counter input clock low pulse width.	$1.5 \times 1/F_{LPD_LSBUS_CTRLMAX}$	—	ns
$F_{TTCICLK}$	Triple-timer counter input clock frequency.	—	$F_{LPD_LSBUS_CTRLMAX}/3$	MHz

Notes:

1. All timing values assume an ideal external input clock. Your actual timing budget must account for additional external clock jitter.

PS Watchdog Timer Interface

Table 55: Watchdog Timer Interface

Symbol	Description	Min	Max	Units
F_{WDTCLK}	Watchdog timer input clock frequency.	—	100	MHz

Table 60: PS-GTR Transceiver Reference Clock Switching Characteristics

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F_{GCLK}	Reference clock frequencies supported.	PCI Express	100 MHz			
		SATA	125 MHz or 150 MHz			
		USB 3.0	26 MHz, 52 MHz, or 100 MHz			
		DisplayPort	27 MHz, 108 MHz, or 135 MHz			
		SGMII	125 MHz			
T_{RCLK}	Reference clock rise time.	20% – 80%	–	200	–	ps
T_{FCLK}	Reference clock fall time.	80% – 20%	–	200	–	ps
T_{DCREF}	Reference clock duty cycle.	Transceiver PLL only.	40	–	60	%
		USB 3.0 with reference clock <40 MHz.	47.5	–	52.5	%

Table 74: Maximum Physical Interface (PHY) Rate for Memory Interfaces (Cont'd)

Memory Standard	Package ⁽¹⁾	DRAM Type	Speed Grade and V _{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
DDR3L	All FFV packages and FBVB900	Single rank component	1866	1866	1866	1866	1600	Mb/s
		1 rank DIMM ⁽²⁾⁽³⁾	1600	1600	1600	1600	1333	Mb/s
		2 rank DIMM ⁽²⁾⁽⁵⁾	1333	1333	1333	1333	1066	Mb/s
		4 rank DIMM ⁽²⁾⁽⁶⁾	800	800	800	800	606	Mb/s
	SFVC784	Single rank component	1600	1600	1600	1600	1600	Mb/s
		1 rank DIMM ⁽²⁾⁽³⁾	1600	1600	1600	1600	1333	Mb/s
		2 rank DIMM ⁽²⁾⁽⁵⁾	1333	1333	1333	1333	1066	Mb/s
		4 rank DIMM ⁽²⁾⁽⁶⁾	800	800	800	800	606	Mb/s
QDR II +	All	Single rank component ⁽⁷⁾	633	633	600	600	550	MHz
RLDRAM 3	All FFV packages and FBVB900	Single rank component	1200	1200	1066	1066	933	MHz
	SFVC784	Single rank component	1066	1066	933	933	800	MHz
QDR IV XP	All	Single rank component	1066	1066	1066	933	933	MHz
LPDDR3	All	Single rank component	1600	1600	1600	1600	1600	Mb/s

Notes:

1. The SBVA484 and SFVA625 packages do not support the PL memory interfaces.
2. Dual in-line memory module (DIMM) includes RDIMM, SODIMM, UDIMM, and LRDIMM.
3. Includes: 1 rank 1 slot, DDP 2 rank, LRDIMM 2 or 4 rank 1 slot.
4. For the DDR4 DDP components at -3 and -2 speed grades and V_{CCINT} = 0.85V, the maximum data rate is 2133 Mb/s for six or more DDP devices. For five or less DDP devices, use the single rank DIMM data rates for the -3 and -2 speed grades at 0.85V.
5. Includes: 2 rank 1 slot, 1 rank 2 slot, LRDIMM 2 rank 2 slot.
6. Includes: 2 rank 2 slot, 4 rank 1 slot.
7. The QDRII+ performance specifications are for burst-length 4 (BL = 4) implementations.

Device Pin-to-Pin Input Parameter Guidelines

The pin-to-pin numbers in [Table 90](#) and [Table 91](#) are based on the clock root placement in the center of the device. The actual pin-to-pin values will vary if the root placement selected is different. Consult the Vivado Design Suite timing report for the actual pin-to-pin values.

Table 90: Global Clock Input Setup and Hold With 3.3V HD I/O without MMCM

Symbol	Description	Device	Speed Grade and V _{CCINT} Operating Voltages					Units	
			0.90V	0.85V		0.72V			
			-3	-2	-1	-2	-1		
Input Setup and Hold Time Relative to Global Clock Input Signal using SSTL15 Standard.(1)(2)(3)									
T _{PSFD_ZU2}	Global clock input and input flip-flop (or latch) without MMCM.	Setup	XCZU2	N/A	2.27	2.37	2.55	2.64	ns
T _{PHFD_ZU2}		Hold			−0.36	−0.36	−0.14	−0.14	ns
T _{PSFD_ZU3}		Setup	XCZU3	N/A	2.27	2.37	2.55	2.64	ns
T _{PHFD_ZU3}		Hold			−0.36	−0.36	−0.14	−0.14	ns
T _{PSFD_ZU4}		Setup	XCZU4	1.28	2.01	2.07	2.59	2.59	ns
T _{PHFD_ZU4}		Hold		−0.28	−0.28	−0.28	−0.09	−0.09	ns
T _{PSFD_ZU5}		Setup	XCZU5	1.28	2.01	2.07	2.59	2.59	ns
T _{PHFD_ZU5}		Hold		−0.28	−0.28	−0.28	−0.09	−0.09	ns
T _{PSFD_ZU6}		Setup	XCZU6	0.96	1.79	1.86	1.93	2.02	ns
T _{PHFD_ZU6}		Hold		−0.05	−0.05	−0.05	0.27	0.42	ns
T _{PSFD_ZU7}		Setup	XCZU7	1.43	2.32	2.42	2.60	2.69	ns
T _{PHFD_ZU7}		Hold		−0.40	−0.40	−0.40	−0.21	−0.21	ns
T _{PSFD_ZU9}		Setup	XCZU9	0.96	1.79	1.86	1.93	2.02	ns
T _{PHFD_ZU9}		Hold		−0.05	−0.05	−0.05	0.27	0.42	ns
T _{PSFD_ZU11}		Setup	XCZU11	1.28	2.01	2.07	2.59	2.59	ns
T _{PHFD_ZU11}		Hold		−0.29	−0.29	−0.29	−0.09	0.19	ns
T _{PSFD_ZU15}		Setup	XCZU15	0.96	1.79	1.85	1.92	2.01	ns
T _{PHFD_ZU15}		Hold		−0.04	−0.04	−0.04	0.27	0.43	ns
T _{PSFD_ZU17}		Setup	XCZU17	1.41	2.29	2.38	2.57	2.65	ns
T _{PHFD_ZU17}		Hold		−0.38	−0.38	−0.38	−0.19	−0.19	ns
T _{PSFD_ZU19}	Setup	XCZU19	1.41	2.29	2.38	2.57	2.65	ns	
T _{PHFD_ZU19}	Hold		−0.38	−0.38	−0.38	−0.19	−0.19	ns	

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, slowest temperature, and slowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, fastest temperature, and fastest voltage.
2. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.

Table 91: Global Clock Input Setup and Hold With MMCM

Symbol	Description	Device	Speed Grade and V _{CCINT} Operating Voltages					Units	
			0.90V	0.85V		0.72V			
			-3	-2	-1	-2	-1		
Input Setup and Hold Time Relative to Global Clock Input Signal using SSTL15 Standard.(1)(2)(3)									
T _{PSMMCMCC_ZU2}	Global clock input and input flip-flop (or latch) with MMCM.	Setup	XCZU2	N/A	1.83	1.96	2.29	2.48	ns
T _{PHMMCMCC_ZU2}		Hold			−0.19	−0.19	0.13	0.13	ns
T _{PSMMCMCC_ZU3}		Setup	XCZU3	N/A	1.83	1.96	2.29	2.48	ns
T _{PHMMCMCC_ZU3}		Hold			−0.19	−0.19	0.13	0.13	ns
T _{PSMMCMCC_ZU4}		Setup	XCZU4	1.96	1.96	2.10	2.49	2.59	ns
T _{PHMMCMCC_ZU4}		Hold		−0.12	−0.12	−0.12	0.27	0.48	ns
T _{PSMMCMCC_ZU5}		Setup	XCZU5	1.96	1.96	2.10	2.49	2.59	ns
T _{PHMMCMCC_ZU5}		Hold		−0.12	−0.12	−0.12	0.27	0.48	ns
T _{PSMMCMCC_ZU6}		Setup	XCZU6	1.97	2.00	2.12	2.26	2.44	ns
T _{PHMMCMCC_ZU6}		Hold		−0.11	−0.11	−0.11	0.16	0.18	ns
T _{PSMMCMCC_ZU7}		Setup	XCZU7	1.91	1.91	2.02	2.45	2.70	ns
T _{PHMMCMCC_ZU7}		Hold		−0.14	−0.14	−0.14	0.37	0.38	ns
T _{PSMMCMCC_ZU9}		Setup	XCZU9	1.97	2.00	2.12	2.26	2.44	ns
T _{PHMMCMCC_ZU9}		Hold		−0.11	−0.11	−0.11	0.16	0.18	ns
T _{PSMMCMCC_ZU11}		Setup	XCZU11	2.08	2.08	2.23	2.59	2.75	ns
T _{PHMMCMCC_ZU11}		Hold		−0.08	−0.08	0.04	0.35	0.74	ns
T _{PSMMCMCC_ZU15}		Setup	XCZU15	1.96	1.99	2.12	2.26	2.44	ns
T _{PHMMCMCC_ZU15}		Hold		−0.10	−0.10	−0.10	0.17	0.19	ns
T _{PSMMCMCC_ZU17}		Setup	XCZU17	1.89	1.89	2.03	2.36	2.55	ns
T _{PHMMCMCC_ZU17}		Hold		−0.16	−0.16	−0.16	0.31	0.34	ns
T _{PSMMCMCC_ZU19}	Setup	XCZU19	1.89	1.89	2.03	2.36	2.55	ns	
T _{PHMMCMCC_ZU19}	Hold		−0.16	−0.16	−0.16	0.31	0.34	ns	

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, slowest temperature, and slowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, fastest temperature, and fastest voltage.
2. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.

GTH Transceiver Switching Characteristics

Consult the *UltraScale Architecture GTH Transceiver User Guide* ([UG576](#)) for further information.

Table 97: GTH Transceiver Performance

Symbol	Description	Output Divider	Speed Grade and V _{CCINT} Operating Voltages										Units
			0.90V		0.85V				0.72V				
			-3		-2		-1		-2		-1		
F _{GTHMAX}	GTH maximum line rate.		16.375 ⁽¹⁾		16.375 ⁽¹⁾		12.5		12.5		10.3125		Gb/s
F _{GTHMIN}	GTH minimum line rate.		0.5		0.5		0.5		0.5		0.5		Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
F _{GTHCRANGE}	CPLL line rate range ⁽²⁾ .	1	4	12.5	4	12.5	4	8.5	4	8.5	4	8.5	Gb/s
		2	2	6.25	2	6.25	2	4.25	2	4.25	2	4.25	Gb/s
		4	1	3.125	1	3.125	1	2.125	1	2.125	1	2.125	Gb/s
		8	0.5	1.5625	0.5	1.5625	0.5	1.0625	0.5	1.0625	0.5	1.0625	Gb/s
		16	N/A										Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
F _{GTHQRANGE1}	QPLL0 line rate range ⁽³⁾ .	1	9.8	16.375	9.8	16.375	9.8	12.5	9.8	12.5	9.8	10.3125	Gb/s
		2	4.9	8.1875	4.9	8.1875	4.9	8.15	4.9	8.1875	4.9	8.15	Gb/s
		4	2.45	4.0938	2.45	4.0938	2.45	4.075	2.45	4.0938	2.45	4.075	Gb/s
		8	1.225	2.0469	1.225	2.0469	1.225	2.0375	1.225	2.0469	1.225	2.0375	Gb/s
		16	0.6125	1.0234	0.6125	1.0234	0.6125	1.0188	0.6125	1.0234	0.6125	1.0188	Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
F _{GTHQRANGE2}	QPLL1 line rate range ⁽⁴⁾ .	1	8.0	13.0	8.0	13.0	8.0	12.5	8.0	12.5	8.0	10.3125	Gb/s
		2	4.0	6.5	4.0	6.5	4.0	6.5	4.0	6.5	4.0	6.5	Gb/s
		4	2.0	3.25	2.0	3.25	2.0	3.25	2.0	3.25	2.0	3.25	Gb/s
		8	1.0	1.625	1.0	1.625	1.0	1.625	1.0	1.625	1.0	1.625	Gb/s
		16	0.5	0.8125	0.5	0.8125	0.5	0.8125	0.5	0.8125	0.5	0.8125	Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
F _{CPLL} RANGE	CPLL frequency range.		2	6.25	2	6.25	2	4.25	2	4.25	2	4.25	GHz
F _{QPLL0} RANGE	QPLL0 frequency range.		9.8	16.375	9.8	16.375	9.8	16.375	9.8	16.375	9.8	16.375	GHz
F _{QPLL1} RANGE	QPLL1 frequency range.		8	13	8	13	8	13	8	13	8	13	GHz

Notes:

1. GTH transceiver line rates in the SFVC784 package support data rates up to 12.5 Gb/s.
2. The values listed are the rounded results of the calculated equation $(2 \times \text{CPLL_Frequency}) / \text{Output_Divider}$.
3. The values listed are the rounded results of the calculated equation $(\text{QPLL0_Frequency}) / \text{Output_Divider}$.
4. The values listed are the rounded results of the calculated equation $(\text{QPLL1_Frequency}) / \text{Output_Divider}$.

Table 98: GTH Transceiver Dynamic Reconfiguration Port (DRP) Switching Characteristics

Symbol	Description	All Speed Grades	Units
F _{GTHDRPCLK}	GTHDRPCLK maximum frequency.	250	MHz

Table 99: GTH Transceiver Reference Clock Switching Characteristics

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F _{GCLK}	Reference clock frequency range.		60	–	820	MHz
T _{RCLK}	Reference clock rise time.	20% – 80%	–	200	–	ps
T _{FCLK}	Reference clock fall time.	80% – 20%	–	200	–	ps
T _{DCREF}	Reference clock duty cycle.	Transceiver PLL only	40	50	60	%

Table 100: GTH Transceiver Reference Clock Oscillator Selection Phase Noise Mask

Symbol	Description	Offset Frequency	Min	Typ	Max	Units
QPLL _{REFCLKMASK} ⁽¹⁾⁽²⁾	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	–	–	–105	dBc/Hz
		100 kHz	–	–	–124	
		1 MHz	–	–	–130	
CPLL _{REFCLKMASK} ⁽¹⁾⁽²⁾	CPLL reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	–	–	–105	dBc/Hz
		100 kHz	–	–	–124	
		1 MHz	–	–	–130	
		50 MHz	–	–	–140	

Notes:

- For reference clock frequencies other than 312.5 MHz, adjust the phase-noise mask values by 20 x Log(N/312.5) where N is the new reference clock frequency in MHz.
- This reference clock phase-noise mask is superseded by any reference clock phase-noise mask that is specified in a supported protocol, e.g., PCIe.

Table 101: GTH Transceiver PLL/Lock Time Adaptation

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
T _{LOCK}	Initial PLL lock.		–	–	1	ms
T _{DLOCK}	Clock recovery phase acquisition and adaptation time for decision feedback equalizer (DFE).	After the PLL is locked to the reference clock, this is the time it takes to lock the clock data recovery (CDR) to the data present at the input.	–	50,000	37 x 10 ⁶	UI
	Clock recovery phase acquisition and adaptation time for low-power mode (LPM) when the DFE is disabled.		–	50,000	2.3 x 10 ⁶	UI

Table 102: GTH Transceiver User Clock Switching Characteristics⁽¹⁾

Symbol	Description	Data Width Conditions (Bit)		Speed Grade and V _{CCINT} Operating Voltages					Units
				0.90V	0.85V		0.72V		
		Internal Logic	Interconnect Logic	-3 ⁽²⁾	-2 ⁽²⁾⁽³⁾	-1 ⁽⁴⁾⁽⁵⁾	-2 ⁽³⁾	-1 ⁽⁵⁾	
F _{TXOUTPMA}	TXOUTCLK maximum frequency sourced from OUTCLKPMA			511.719	511.719	390.625	390.625	322.266	MHz
F _{RXOUTPMA}	RXOUTCLK maximum frequency sourced from OUTCLKPMA			511.719	511.719	390.625	390.625	322.266	MHz

Table 104: GTH Transceiver Receiver Switching Characteristics (Cont'd)

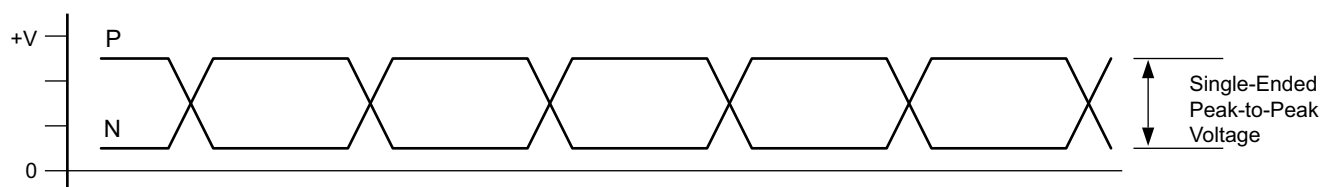
Symbol	Description	Condition	Min	Typ	Max	Units
J _{T_SJ2.5}	Sinusoidal jitter (CPLL) ⁽³⁾	2.5 Gb/s ⁽⁵⁾	0.30	–	–	UI
J _{T_SJ1.25}	Sinusoidal jitter (CPLL) ⁽³⁾	1.25 Gb/s ⁽⁶⁾	0.30	–	–	UI
J _{T_SJ500}	Sinusoidal jitter (CPLL) ⁽³⁾	500 Mb/s ⁽⁷⁾	0.30	–	–	UI
SJ Jitter Tolerance with Stressed Eye⁽²⁾						
J _{T_TJSE3.2}	Total jitter with stressed eye ⁽⁸⁾	3.2 Gb/s	0.70	–	–	UI
J _{T_TJSE6.6}		6.6 Gb/s	0.70	–	–	UI
J _{T_SJSE3.2}	Sinusoidal jitter with stressed eye ⁽⁸⁾	3.2 Gb/s	0.10	–	–	UI
J _{T_SJSE6.6}		6.6 Gb/s	0.10	–	–	UI

Notes:

- Using RXOUT_DIV = 1, 2, and 4.
- All jitter values are based on a bit error ratio of 10^{–12}.
- The frequency of the injected sinusoidal jitter is 80 MHz.
- CPLL frequency at 3.2 GHz and RXOUT_DIV = 2.
- CPLL frequency at 2.5 GHz and RXOUT_DIV = 2.
- CPLL frequency at 2.5 GHz and RXOUT_DIV = 4.
- CPLL frequency at 2.0 GHz and RXOUT_DIV = 8.
- Composite jitter with RX equalizer enabled. DFE disabled.

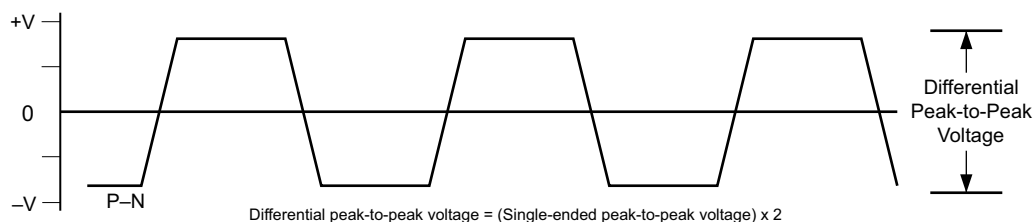
GTH Transceiver Electrical Compliance

The *UltraScale Architecture GTH Transceiver User Guide* ([UG576](#)) contains recommended use modes that ensure compliance for the protocols listed in [Table 105](#). The transceiver wizard provides the recommended settings for those use cases and for protocol specific characteristics.



X16653-101316

Figure 5: Single-Ended Peak-to-Peak Voltage



X16639-101316

Figure 6: Differential Peak-to-Peak Voltage

Table 107 and Table 108 summarize the DC specifications of the clock input of the GTY transceivers in Zynq UltraScale+ MPSoCs. Consult the *UltraScale Architecture GTY Transceiver User Guide* ([UG578](#)) for further details.

Table 107: GTY Transceiver Clock DC Input Level Specification

Symbol	DC Parameter	Min	Typ	Max	Units
V_{IDIFF}	Differential peak-to-peak input voltage	250	–	2000	mV
R_{IN}	Differential input resistance	–	100	–	Ω
C_{EXT}	Required external AC coupling capacitor	–	10	–	nF

Table 108: GTY Transceiver Clock Output Level Specification

Symbol	Description	Conditions	Min	Typ	Max	Units
V_{OL}	Output Low voltage for P and N	$R_T = 100\Omega$ across P and N signals	100	–	330	mV
V_{OH}	Output High voltage for P and N	$R_T = 100\Omega$ across P and N signals	500	–	700	mV
V_{DDOUT}	Differential output voltage (P–N), P = High (N–P), N = High	$R_T = 100\Omega$ across P and N signals	300	–	430	mV
V_{CMOUT}	Common mode voltage	$R_T = 100\Omega$ across P and N signals	300	–	500	mV

Table 113: GTY Transceiver PLL /Lock Time Adaptation

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
T _{LOCK}	Initial PLL lock.		–	–	1	ms
T _{DLOCK}	Clock recovery phase acquisition and adaptation time for decision feedback equalizer (DFE).	After the PLL is locked to the reference clock, this is the time it takes to lock the clock data recovery (CDR) to the data present at the input.	–	50,000	37 x 10 ⁶	UI
	Clock recovery phase acquisition and adaptation time for low-power mode (LPM) when the DFE is disabled.		–	50,000	2.3 x 10 ⁶	UI

Table 114: GTY Transceiver User Clock Switching Characteristics⁽¹⁾

Symbol	Description	Data Width Conditions (Bit)		Speed Grade and V _{CCINT} Operating Voltages					Units
				0.90V	0.85V		0.72V		
		Internal Logic	Interconnect Logic	-3 ⁽²⁾	-2 ⁽²⁾⁽³⁾	-1 ⁽⁴⁾⁽⁵⁾	-2 ⁽³⁾	-1 ⁽⁵⁾	
F _{TXOUTPMA}	TXOUTCLK maximum frequency sourced from OUTCLKPMA			511.719	511.719	402.833	402.833	322.266	MHz
F _{RXOUTPMA}	RXOUTCLK maximum frequency sourced from OUTCLKPMA			511.719	511.719	402.833	402.833	322.266	MHz
F _{TXOUTPROGDIV}	TXOUTCLK maximum frequency sourced from TXPROGDIVCLK			511.719	511.719	511.719	511.719	511.719	MHz
F _{RXOUTPROGDIV}	RXOUTCLK maximum frequency sourced from RXPROGDIVCLK			511.719	511.719	511.719	511.719	511.719	MHz
F _{TXIN}	TXUSRCLK ⁽⁶⁾ maximum frequency	16	16, 32	511.719	511.719	390.625	390.625	322.266	MHz
		32	32, 64	511.719	511.719	390.625	390.625	322.266	MHz
		64	64, 128	511.719	440.781	402.832	402.832	195.313	MHz
		20	20, 40	409.375	409.375	312.500	312.500	257.813	MHz
		40	40, 80	409.375	409.375	312.500	350.000	257.813	MHz
		80	80, 160	409.375	352.625	322.266	352.625	156.250	MHz
F _{RXIN}	RXUSRCLK ⁽⁶⁾ maximum frequency	16	16, 32	511.719	511.719	390.625	390.625	322.266	MHz
		32	32, 64	511.719	511.719	390.625	390.625	322.266	MHz
		64	64, 128	511.719	440.781	402.832	402.832	195.313	MHz
		20	20, 40	409.375	409.375	312.500	312.500	257.813	MHz
		40	40, 80	409.375	409.375	312.500	350.000	257.813	MHz
		80	80, 160	409.375	352.625	322.266	352.625	156.250	MHz

Table 116: GTY Transceiver Receiver Switching Characteristics

Symbol	Description	Condition	Min	Typ	Max	Units	
F _{GTYRX}	Serial data rate		0.500	–	F _{GTYMAX}	Gb/s	
R _{XSSST}	Receiver spread-spectrum tracking ⁽¹⁾		Modulated at 33 kHz	–5000	–	0	ppm
R _{XRL}	Run length (CID)			–	–	256	UI
R _{XPPMTOL}	Data/REFCLK PPM offset tolerance	Bit rates ≤ 6.6 Gb/s	–1250	–	1250	ppm	
		Bit rates > 6.6 Gb/s and ≤ 8.0 Gb/s	–700	–	700	ppm	
		Bit rates > 8.0 Gb/s	–200	–	200	ppm	
SJ Jitter Tolerance ⁽²⁾							
J _{T_SJ32.75}	Sinusoidal jitter (QPLL) ⁽³⁾	32.75 Gb/s	0.25	–	–	UI	
J _{T_SJ28.21}	Sinusoidal jitter (QPLL) ⁽³⁾	28.21 Gb/s	0.30	–	–	UI	
J _{T_SJ16.375}	Sinusoidal jitter (QPLL) ⁽³⁾	16.375 Gb/s	0.30	–	–	UI	
J _{T_SJ15.0}	Sinusoidal jitter (QPLL) ⁽³⁾	15.0 Gb/s	0.30	–	–	UI	
J _{T_SJ14.1}	Sinusoidal jitter (QPLL) ⁽³⁾	14.1 Gb/s	0.30	–	–	UI	
J _{T_SJ13.1}	Sinusoidal jitter (QPLL) ⁽³⁾	13.1 Gb/s	0.30	–	–	UI	
J _{T_SJ12.5}	Sinusoidal jitter (QPLL) ⁽³⁾	12.5 Gb/s	0.30	–	–	UI	
J _{T_SJ11.3}	Sinusoidal jitter (QPLL) ⁽³⁾	11.3 Gb/s	0.30	–	–	UI	
J _{T_SJ10.32_QPLL}	Sinusoidal jitter (QPLL) ⁽³⁾	10.32 Gb/s	0.30	–	–	UI	
J _{T_SJ10.32_CPLL}	Sinusoidal jitter (CPLL) ⁽³⁾	10.32 Gb/s	0.30	–	–	UI	
J _{T_SJ9.953_QPLL}	Sinusoidal jitter (QPLL) ⁽³⁾	9.953 Gb/s	0.30	–	–	UI	
J _{T_SJ9.953_CPLL}	Sinusoidal jitter (CPLL) ⁽³⁾	9.953 Gb/s	0.30	–	–	UI	
J _{T_SJ8.0}	Sinusoidal jitter (CPLL) ⁽³⁾	8.0 Gb/s	0.42	–	–	UI	
J _{T_SJ6.6}	Sinusoidal jitter (CPLL) ⁽³⁾	6.6 Gb/s	0.44	–	–	UI	
J _{T_SJ5.0}	Sinusoidal jitter (CPLL) ⁽³⁾	5.0 Gb/s	0.44	–	–	UI	
J _{T_SJ4.25}	Sinusoidal jitter (CPLL) ⁽³⁾	4.25 Gb/s	0.44	–	–	UI	
J _{T_SJ3.2}	Sinusoidal jitter (CPLL) ⁽³⁾	3.2 Gb/s ⁽⁴⁾	0.45	–	–	UI	
J _{T_SJ2.5}	Sinusoidal jitter (CPLL) ⁽³⁾	2.5 Gb/s ⁽⁵⁾	0.30	–	–	UI	
J _{T_SJ1.25}	Sinusoidal jitter (CPLL) ⁽³⁾	1.25 Gb/s ⁽⁶⁾	0.30	–	–	UI	
J _{T_SJ500}	Sinusoidal jitter (CPLL) ⁽³⁾	500 Mb/s ⁽⁷⁾	0.30	–	–	UI	
SJ Jitter Tolerance with Stressed Eye ⁽²⁾							
J _{T_TJSE3.2}	Total jitter with stressed eye ⁽⁸⁾	3.2 Gb/s	0.70	–	–	UI	
J _{T_TJSE6.6}		6.6 Gb/s	0.70	–	–	UI	
J _{T_SJSE3.2}	Sinusoidal jitter with stressed eye ⁽⁸⁾	3.2 Gb/s	0.10	–	–	UI	
J _{T_SJSE6.6}		6.6 Gb/s	0.10	–	–	UI	

Notes:

- Using RXOUT_DIV = 1, 2, and 4.
- All jitter values are based on a bit error ratio of 10^{–12}.
- The frequency of the injected sinusoidal jitter is 80 MHz.
- CPLL frequency at 3.2 GHz and RXOUT_DIV = 2.
- CPLL frequency at 2.5 GHz and RXOUT_DIV = 2.
- CPLL frequency at 2.5 GHz and RXOUT_DIV = 4.
- CPLL frequency at 2.0 GHz and RXOUT_DIV = 8.
- Composite jitter with RX equalizer enabled. DFE disabled.

Integrated Interface Block for Interlaken

More information and documentation on solutions using the integrated interface block for Interlaken can be found at [UltraScale+ Interlaken](#). The *UltraScale Architecture and Product Overview* (DS890) lists how many blocks are in each Zynq UltraScale+ MPSoC. This section describes the following Interlaken configurations.

- 12 x 12.5 Gb/s protocol and lane logic mode ([Table 118](#)).
- 6 x 25.78125 Gb/s and 6 x 28.21 Gb/s protocol and lane logic mode ([Table 119](#)).
- 12 x 25.78125 Gb/s lane logic only mode ([Table 120](#)).

Zynq UltraScale+ MPSoCs in the SFVB784, FFVA676, and FFVA1156 packages are only supported using the 12 x 12.5 Gb/s Interlaken configuration. See [Table 109](#) for the F_{GTYMAX} description.

Table 118: Maximum Performance for Interlaken 12 x 12.5 Gb/s Protocol and Lane Logic Mode Designs

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages										Units
		0.90V		0.85V				0.72V				
		-3		-2		-1		-2		-1		
F _{RX_SERDES_CLK}	Receive serializer/ deserializer clock	195.32		195.32		195.32		195.32		195.32		MHz
F _{TX_SERDES_CLK}	Transmit serializer/ deserializer clock	195.32		195.32		195.32		195.32		195.32		MHz
F _{DRP_CLK}	Dynamic reconfiguration port clock	250.00		250.00		250.00		250.00		250.00		MHz
		Min ⁽¹⁾	Max	Min ⁽¹⁾	Max	Min ⁽¹⁾	Max	Min ⁽¹⁾	Max	Min ⁽¹⁾	Max	
F _{CORE_CLK}	Interlaken core clock	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	MHz
F _{LBUS_CLK}	Interlaken local bus clock	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	MHz

Notes:

1. These are the minimum clock frequencies at the maximum lane performance.

Video Codec Performance

The *UltraScale Architecture and Product Overview* ([DS890](#)) lists the Zynq UltraScale+ MPSoC EV devices that include the Video Codec unit (VCU).

Table 123: VCU Performance

Description	Speed Grade and V _{CCINT} Operating Voltages					Units
	0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	
Video Codec decoder block maximum frequency (H.264/5 10-bit 4:2:2)	667	667	667	667	667	MHz

PL System Monitor Specifications

Table 124: PL SYSMON Specifications

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
V _{CCADC} = 1.8V ±3%, V _{REFP} = 1.25V, V _{REFN} = 0V, ADCCLK = 5.2 MHz, T _j = −40°C to 100°C, typical values at T _j = 40°C						
ADC Accuracy ⁽¹⁾						
Resolution			10	–	–	Bits
Integral nonlinearity ⁽²⁾	INL		–	–	±1.5	LSBs
Differential nonlinearity	DNL	No missing codes, guaranteed monotonic	–	–	±1	LSBs
Offset error		Offset calibration enabled	–	–	±2	LSBs
Gain error			–	–	±0.4	%
Sample rate			–	–	0.2	MS/s
RMS code noise		External 1.25V reference	–	–	1	LSBs
		On-chip reference	–	1	–	LSBs
ADC Accuracy at Extended Temperatures						
Resolution		T _j = −55°C to 125°C	10	–	–	Bits
Integral nonlinearity ⁽²⁾	INL	T _j = −55°C to 125°C	–	–	±1.5	LSBs
Differential nonlinearity	DNL	No missing codes, guaranteed monotonic (T _j = −55°C to 125°C)	–	–	±1	
Analog Inputs ⁽²⁾						
ADC input ranges		Unipolar operation	0	–	1	V
		Bipolar operation	−0.5	–	+0.5	V
		Unipolar common mode range (FS input)	0	–	+0.5	V
		Bipolar common mode range (FS input)	+0.5	–	+0.6	V
Maximum external channel input ranges		Adjacent channels set within these ranges should not corrupt measurements on adjacent channels	−0.1	–	V _{CCADC}	V

Configuration Switching Characteristics

Table 127: Configuration Switching Characteristics

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
PL Power-up Timing Characteristics							
T _{PL}	PS_PROG_B PL latency.	7.5	7.5	7.5	7.5	7.5	ms, Max
T _{POR}	Power-on reset from PL power-on to PL ready to configure (40 ms maximum ramp rate).	65	65	65	65	65	ms, Max
		0	0	0	0	0	ms, Min
	Power-on reset from PL power-on to PL ready to configure with POR override (2 ms maximum ramp rate).	15	15	15	15	15	ms, Max
		5	5	5	5	5	ms, Min
T _{PS_PROG_B}	PL program pulse width.	250	250	250	250	250	ns, Min
Internal Configuration Access Port							
F _{ICAPCK}	Internal configuration access port (ICAPE3).	200	200	200	150	150	MHz, Max
DNA Port Switching							
F _{DNACK}	DNA port frequency (DNA_PORT).	200	200	200	175	175	MHz, Max
STARTUPE3 Ports							
F _{CFGMCLK}	STARTUPE3 CFGMCLK output frequency.	50.00	50.00	50.00	50.00	50.00	MHz, Typ
F _{CFGMCLKTOL}	STARTUPE3 CFGMCLK output frequency tolerance.	±15	±15	±15	±15	±15	%, Max
T _{DCI_MATCH}	Specifies a stall in the startup cycle until the digitally controlled impedance (DCI) match signals are asserted.	4	4	4	4	4	ms, Max